### **Vishay Semiconductors**

Hyperfast Rectifier, 20 A FRED Pt<sup>®</sup> G5



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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub> 20 A									
V <sub>R</sub>	1200 V								
V <sub>F</sub> at I <sub>F</sub> at 125 °C	2.40 V								
t <sub>rr</sub>	29 ns								
T <sub>J</sub> max.	175 °C								
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)								
Circuit configuration	Single								

#### **FEATURES**

- Hyperfast and optimized Q<sub>rr</sub>
- Best in class forward voltage drop and switching RoHS
   losses trade off
   COMPLIANT
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245  $^{\circ}\mathrm{C}$
- Designed and qualified according to JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

#### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 88 °C	20							
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 88 °C, D = 0.50, f = 20 kHz	33	А						
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_C = 45$ °C, $t_p = 10$ ms, sine wave	110							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS					UNITS				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	1200	-	-					
	V <sub>F</sub>	I <sub>F</sub> = 20 A	-	2.71	3.6	V				
Forward voltage		I <sub>F</sub> = 20 A, T <sub>J</sub> = 125 °C	-	2.40	-					
Povereo lookago ourrent	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	50					
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	10	-	pF				
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH				

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 1
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J$ = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, dI_F/d$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$			-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	115	-	20			
		T <sub>J</sub> = 125 °C		-	170	-	ns			
Peak recovery current	1	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 12 A dl <sub>F</sub> /dt = 600 A/µs	-	10	-	A			
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	16	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	430	-	nC			
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	1045	-				
Reverse recovery time	1	T <sub>J</sub> = 25 °C		-	93	-	ns			
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	122	-				
Peak recovery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 1000 A/µs	-	21	-	A			
Peak recovery current		T <sub>J</sub> = 125 °C	$V_{\rm B} = 800 \text{ V}$	-	32	-				
Poverse recovery oberge	0	T <sub>J</sub> = 25 °C		-	850	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2020	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.7	°C/W				
Weight			-	2.0	-	g				
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C				
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)	E5TX2112S							

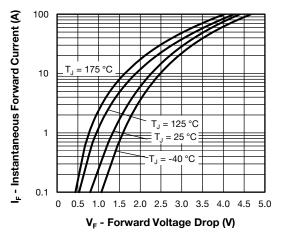


Fig. 1 - Forward Voltage Drop Characteristics

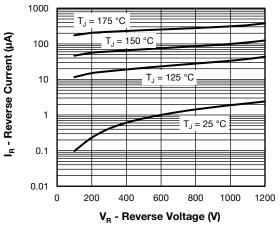


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



## VS-E5TX2112S2L-M3

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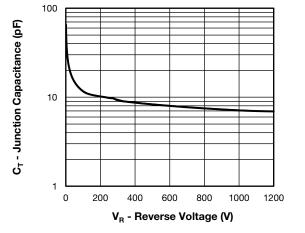


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

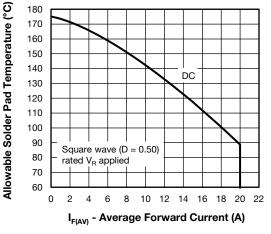


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

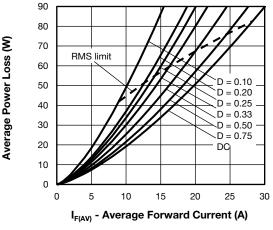


Fig. 5 - Forward Power Loss Characteristics

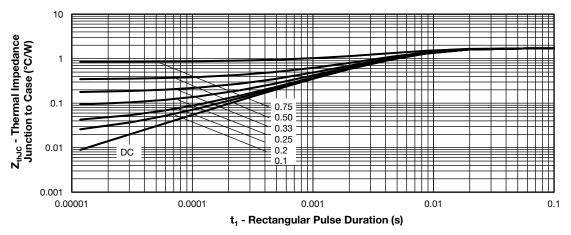


Fig. 6 - Transient Thermal Impedance, Junction to Case

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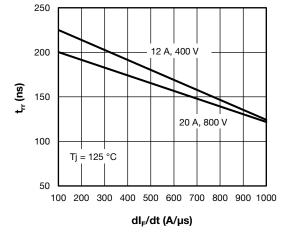
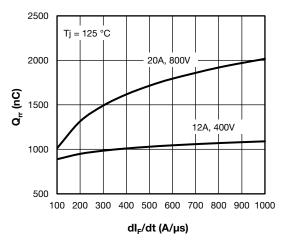
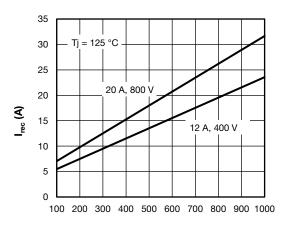


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt







**dl<sub>F</sub>/dt (A/μs)** Fig. 9 - Typical Stored Charge vs. dl<sub>F</sub>/dt



# VS-E5TX2112S2L-M3

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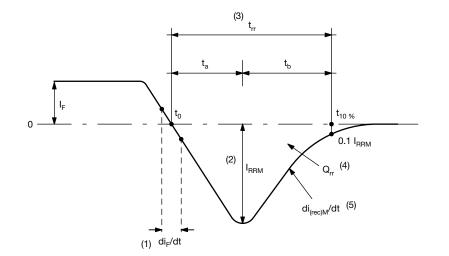


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Notes

- $^{(1)}~di_{F}/dt$  rate of change of current through zero crossing
- $^{(2)}\ \ I_{RRM}$  peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10} \%} I(t) dt$$

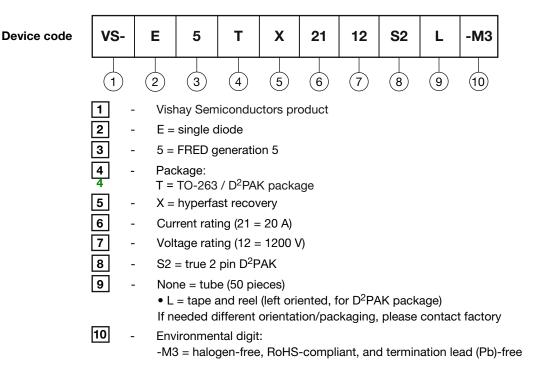
 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>



### **Vishay Semiconductors**

**ORDERING INFORMATION TABLE** 

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ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-E5TX2112S2L-M3	800	13" diameter reel							

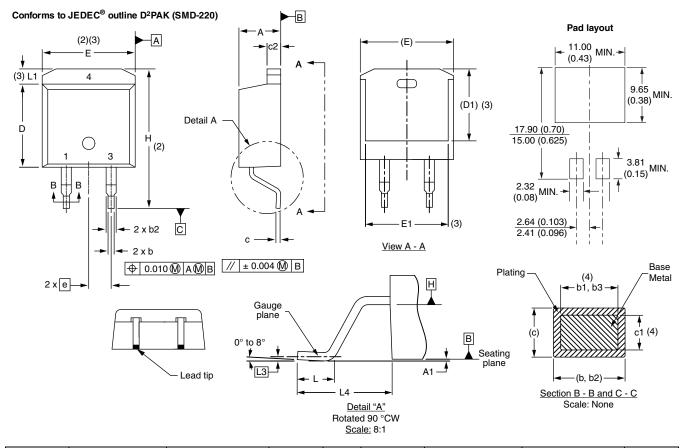
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						

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D<sup>2</sup>PAK 2L (TO-263AB 2L)

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L3	0.25 BSC 0		0.010	BSC	
c2	1.14	1.65	0.045	0.065		L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2						

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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